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P	ATENT COOPERATION TREA	TV
	PCT	WIPO PCT
TERNATI	ONAL PRELIMINARY REPORT ON PA	TENTABILITY
	(Chapter II of the Patent Cooperation Treat	dy)
AL PASSION OF THE PAS	(PCT Article 36 and Rule 70)	
Applicant's or agent's file reference BUR920030082	FOR FURTHER ACTION	See Form PCT/IPEA/416
International application No.	International filing date (day/month/year)	Priority date (day/month/year)
PCT/US03/39026	08 December 2003 (08.12.2003)	
International Patent Classification (IPC)	or national classification and IPC	
IPC(7): H01L 27/148 and US Cl.: 257/	/250,270,333,340,347,365,386,406,903	
Applicant		
INTERNATIONAL BUSINESS MACI		
1. This report is the international Examining Authority und	ational preliminary examination report, establer Article 35 and transmitted to the applican	plished by this International Preliminary t according to Article 36.
2. This REPORT consists of	of a total of sheets, including this cover s	heet.
This report is also accom	panied by ANNEXES, comprising:	
a. (sent to the applic	cant and to the International Bureau) a total (of sheets, as follows:
	ne description, claims and/or drawings which	
of this rep	ort and/or sheets containing rectifications a	uthorized by this Authority (see Rule
70.16 and 5	Section 607 of the Administrative Instruction	s).
sheets wh	nich supersede earlier sheets, but which	this Authority considers contain an
amendment	t that goes beyond the disclosure in the nitem 4 of Box No. I and the Supplemental I	international application as filed, as
	ernational Bureau only) a total of (indicate ty	
. contair	ning a sequence listing and/or tables related the Supplemental Box Relating to Sequen	d thereto, in electronic form only, as
	ications relating to the following items:	
K 7 1	Basis of the report	
	•	
	Priority	
	Non-establishment of opinion with regard to applicability	novelty, inventive step and industrial
Box No. IV	Lack of unity of invention	
Bax No. V	Reasoned statement under Article 35(2) windustrial applicability; citations and explana	ith regard to novelty, inventive step or
_	Certain documents cited	
Box No. VII	Certain defects in the international application	on
Box No. VIII	Certain observations on the international app	plication
Date of submission of the demand	Date of complet	ion of this report
08 July 2005 (08.07.2005)	17 October 2005	(17.10.2005)
Name and mailing address of the IPE	A/ US Authorized office	We lot
Mail Stop PCT, Attn: IPEA/US Commissioner for Patents	S David Nelm	Lainne Caile
P.O. Box 1450 Alexandria, Virginia 22313-14	••	lan -
Facsimile No. (703)305-3230	Telephone 140. (703)308-0956
Form PCT/IPEA/409 (cover sheet)(Ap	ril 2005)	

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No.	
PCT/US03/39026	

Dow No		Basis of the report
K 7		ard to the language, this report is based on: international application in the language in which it was filed.
×		
	a tr	anslation of the international application into <u>English</u> , which is the language of a translation furnished for purposes of:
		international search (under Rules 12.3 and 23.1(b))
		publication of the international application (under Rule 12.4(a))
		international preliminary examination (under Rules 55.2(a) and/or 55.3(a))
furni	shed	gard to the elements of the international application, this report is based on (replacement sheets which have been to the receiving Office in response to an invitation under Article 14 are referred to in this report as "originally filed" not annexed to this report):
\boxtimes	the	e international application as originally filed/furnished
\boxtimes	the	e description:
	pa	ges 1-7 as originally filed/furnished ges* NONE received by this Authority on
	pa	ges* NONE received by this Authority on
\boxtimes		e claims:
	na	ges 8 and 9 as originally filed/furnished
	na	ges* NONE as amended (together with any statement) under Article 19
	pa	ges* NONE received by this Authority on received by the received by th
	•	ges* NONE received by this Addiorny on
	th	e drawings:
]	-	ages 1/4-4/4 as originally filed/furnished received by this Authority on
		ages* NONE received by this Authority on
	•	sequence listing and/or any related table(s) - see Supplemental Box Relating to Sequence Listing.
} <u> </u>	_ ~	sequence noting and of any course many,
3. 🗵	т [he amendments have resulted in the cancellation of:
		the description, pages None
	Ď	the claims, Nos None
	Ī	the drawings, sheets/figs_None
	Ī	the sequence listing (specify): None.
	Ī	any table(s) related to the sequence listing (specify): None
4.	٦ 4	This report has been established as if (some of) the amendments annexed to this report and listed below had not been made, ince they have been considered to go beyond the disclosure as filed, as indicated in the Supplemental Box (Rule 70.2(c)).
	ſ	the description, pages .
1	j	the claims, Nos.
	i	the drawings, sheets/figs
	Ì	the sequence listing (specify):
		any table(s) related to the sequence listing (specify):
	4	4 applies, some or all of those sheets may be marked "superseded."
* If it	em	4 applies, some or all of those sneets may be marked supersetted.

Form PCT/IPEA/409 (Box No. I) (April 2005)

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

Form PCT/IPEA/409 (Box No. V) (April 2005)

International application No. PCT/US03/39026

Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement						
1. Statement						
Novelty (N)	Claims	1-11	YES			
, co	Claims	NONE	_NO			
			YES			
Inventive Step (IS)		1-11 NONE	_NO			
	Ciaims	NONE	-1.0			
Industrial Applicability (IA)	Claims	1-11	_YES			
	Claims	NONE	_ио			
the second dielectric layer at least partly covering the s layer provides a gate capacitance of a gate formed over theoretical capacitance of a gate formed over the first of independent Claim 1.	second porter the second dielectric la	layer having property different from the first dielectric layer tion of the substrate, wherein the property of the second died dielectric layer with respect to the substrate that is greater ayer, and in combination with all other features as recited in because an integrated circuit semiconductor memory devictly.	than a			